

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$ $T_A = 25^\circ C$
-40V	51m $\Omega$ @ $V_{GS} = -10V$	-10.5A
	85m $\Omega$ @ $V_{GS} = -4.5V$	-8.4A

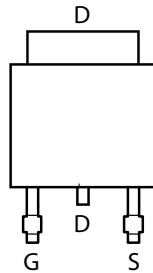
## Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

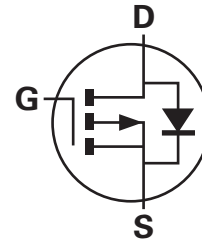
- Backlighting
- DC-DC Converters
- Power management functions



Top View



Pin Out -Top View



Equivalent Circuit

## Features and Benefits

- Low on-resistance
- Fast switching speed
- "Green" component and RoHS compliant (Note 1)

## Mechanical Data

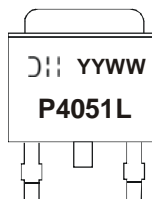
- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Below
- Ordering Information: See Below
- Weight: 0.33 grams (approximate)

## Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMP4051LK3-13	P4051L	13	16	2,500

Note: 1. Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

## Marking Information



⌋⌋⌋ = Manufacturer's Marking  
 P4051L = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 09 = 2009)  
 WW = Week (01-52)

**Maximum Ratings** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

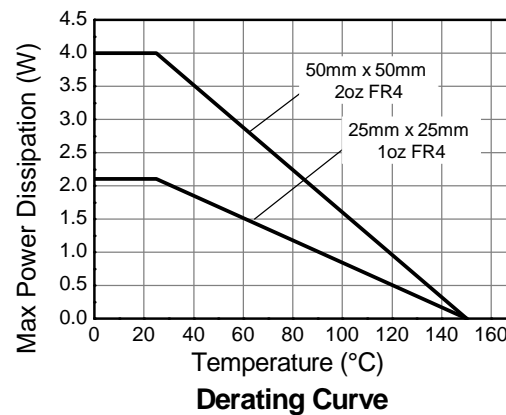
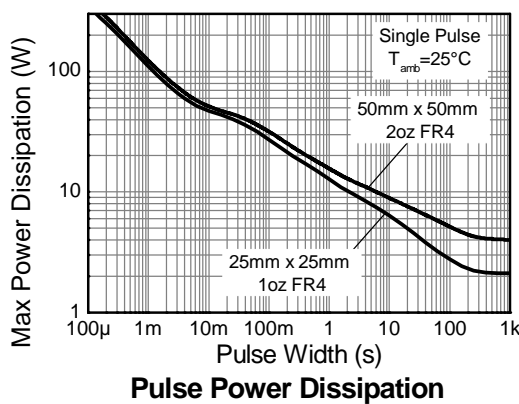
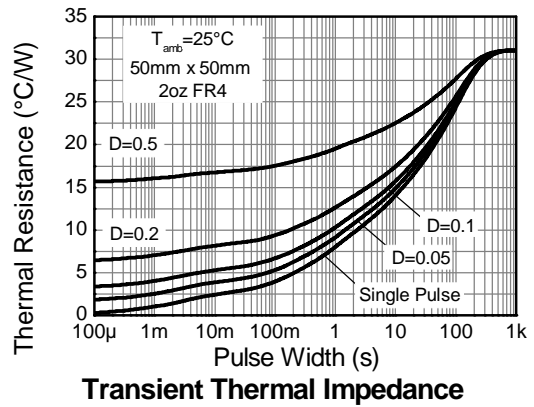
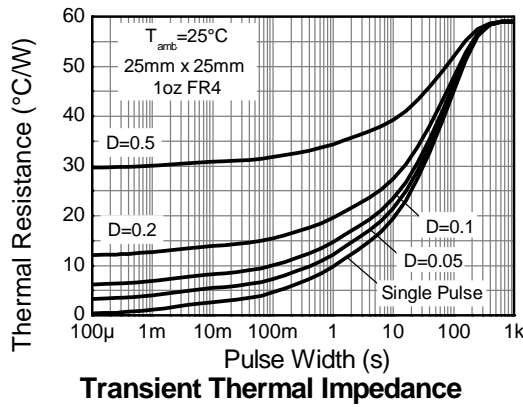
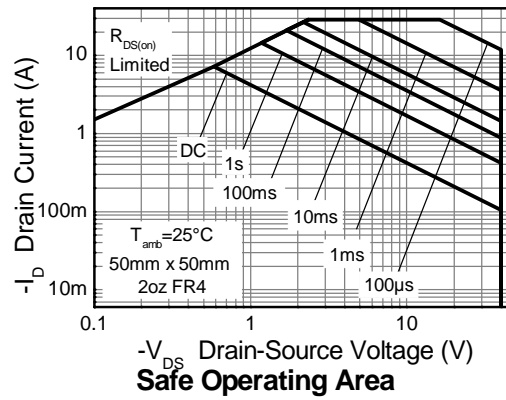
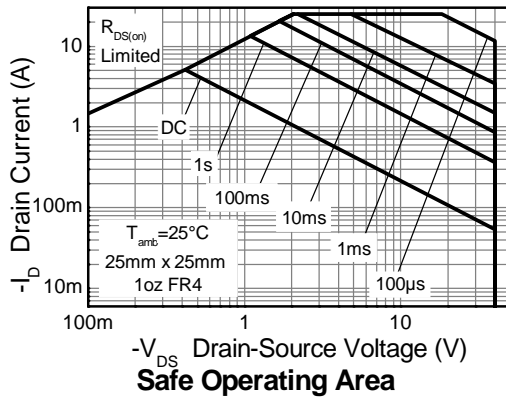
Characteristic		Symbol	Value	Unit	
Drain-Source voltage		$V_{DSS}$	-40	V	
Gate-Source voltage		$V_{GS}$	$\pm 20$	V	
Continuous Drain current	$V_{GS} = 10\text{V}$	(Note 3)	-10.5	A	
		$T_A = 70^\circ\text{C}$ (Note 3)	-8.40		
		(Note 2)	-7.2		
Pulsed Drain current	$V_{GS} = 10\text{V}$	(Note 4)	$I_{DM}$	-28.9	A
Continuous Source current (Body diode)		(Note 3)	$I_S$	-10.1	A
Pulsed Source current (Body diode)		(Note 4)	$I_{SM}$	-28.9	A

**Thermal Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Note 2)	$P_D$	4.18	W mW/ $^\circ\text{C}$
			33.4	
	(Note 3)		8.9	
			71.4	
	(Note 5)		2.14	
Thermal Resistance, Junction to Ambient	(Note 2)	$R_{\theta JA}$	29.9	$^\circ\text{C/W}$
	(Note 3)		14.0	
	(Note 5)		58.4	
Thermal Resistance, Junction to Lead	(Note 6)	$R_{\theta JL}$	2.46	
Operating and storage temperature range		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

- Notes:
2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  3. Same as note 2, except the device is measured at  $t \leq 10$  sec.
  4. Same as note 2, except the device is pulsed with  $D = 0.02$  and pulse width 300  $\mu\text{s}$ . The pulse current is limited by the maximum junction temperature.
  5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  6. Thermal resistance from junction to solder-point (at the end of the drain lead).

**Thermal Characteristics**

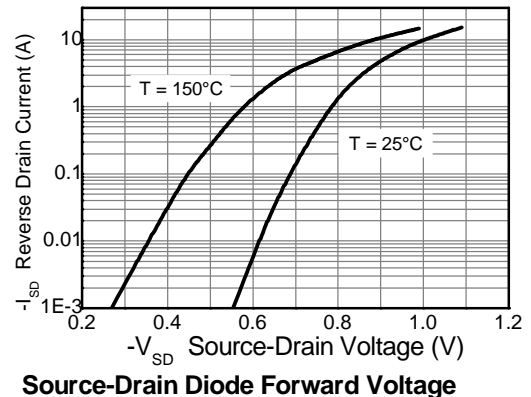
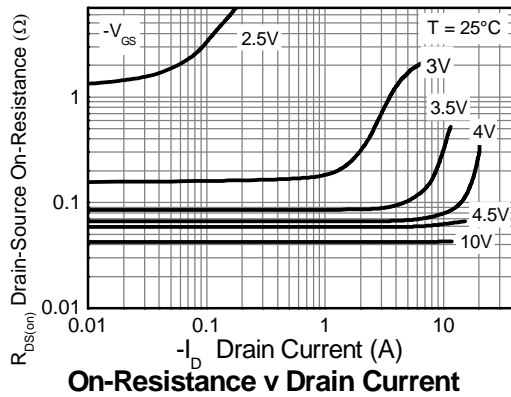
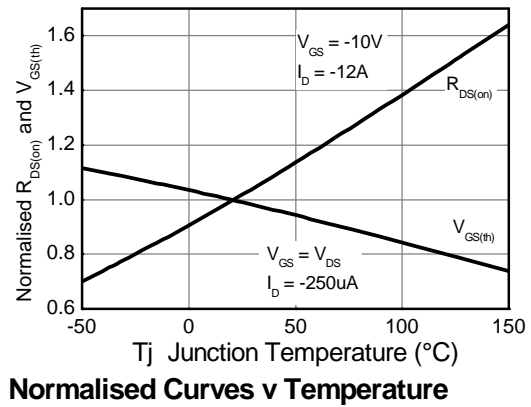
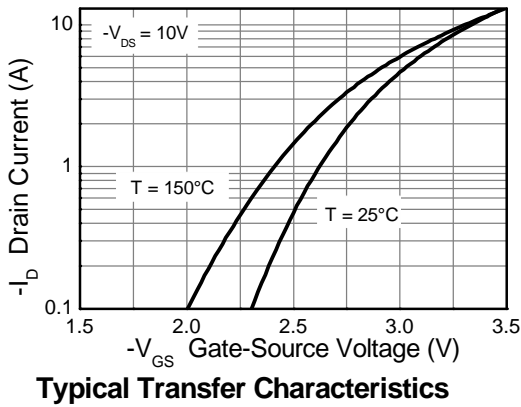
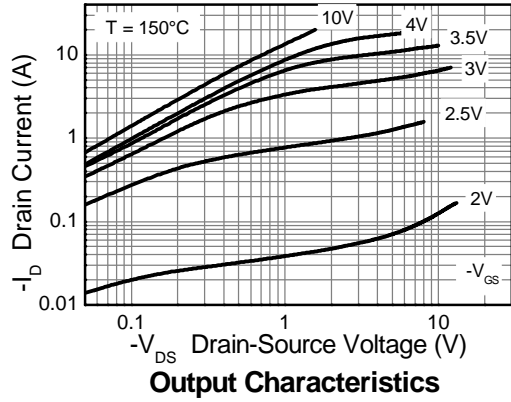
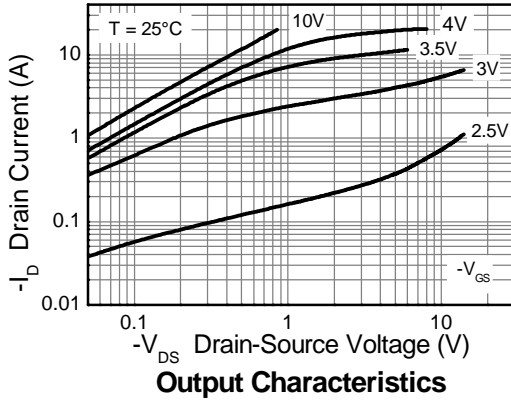


**Electrical Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

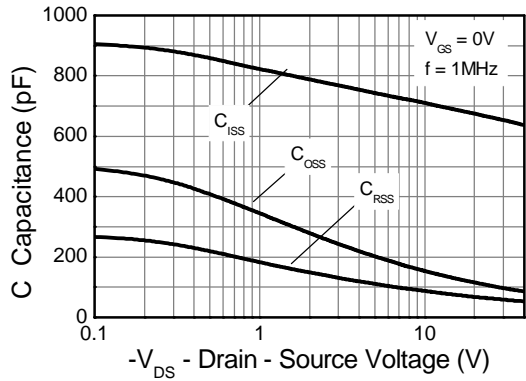
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-40	—	—	V	$I_D = -250\mu\text{A}$ , $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	-0.5	$\mu\text{A}$	$V_{DS} = -40\text{V}$ , $V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	—	-3.0	V	$I_D = -250\mu\text{A}$ , $V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 7)	$R_{DS(on)}$	—	—	0.051	$\Omega$	$V_{GS} = -10\text{V}$ , $I_D = -12\text{A}$
				0.085		$V_{GS} = -4.5\text{V}$ , $I_D = -8\text{A}$
Forward Transconductance (Notes 7 & 8)	$g_{fs}$	—	16.6	—	S	$V_{DS} = -15\text{V}$ , $I_D = -12\text{A}$
Diode Forward Voltage (Note 7)	$V_{SD}$	—	-0.98	-1.2	V	$I_S = -12\text{A}$ , $V_{GS} = 0\text{V}$
Reverse recovery time (Note 8)	$t_{rr}$	—	138	—	ns	$I_S = -12\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$
Reverse recovery charge (Note 8)	$Q_{rr}$	—	841	—	nC	
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	—	674	—	pF	$V_{DS} = -20\text{V}$ , $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	$C_{oss}$	—	115	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	67.7	—	pF	
Total Gate Charge	$Q_g$	—	7.0	—	nC	$V_{GS} = -4.5\text{V}$
Total Gate Charge	$Q_g$	—	14	—	nC	$V_{GS} = -10\text{V}$
Gate-Source Charge	$Q_{gs}$	—	2.2	—	nC	
Gate-Drain Charge	$Q_{gd}$	—	3.7	—	nC	
Turn-On Delay Time (Note 9)	$t_{D(on)}$	—	2.3	—	ns	$V_{DD} = -20\text{V}$ , $V_{GS} = -10\text{V}$ $I_D = -12\text{A}$ , $R_G \cong 6.0\Omega$
Turn-On Rise Time (Note 9)	$t_r$	—	14.1	—	ns	
Turn-Off Delay Time (Note 9)	$t_{D(off)}$	—	25.1	—	ns	
Turn-Off Fall Time (Note 9)	$t_f$	—	14.3	—	ns	

- Notes:
7. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$
  8. For design aid only, not subject to production testing.
  9. Switching characteristics are independent of operating junction temperatures.

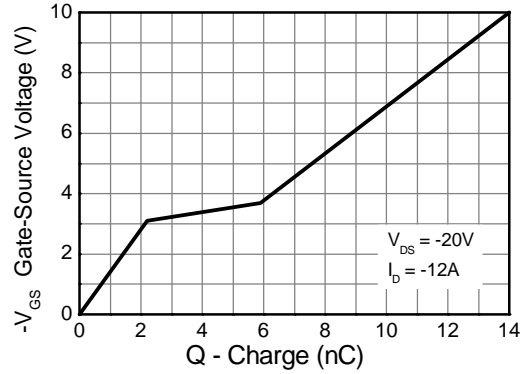
**Typical Characteristics**



**Typical Characteristics - continued**

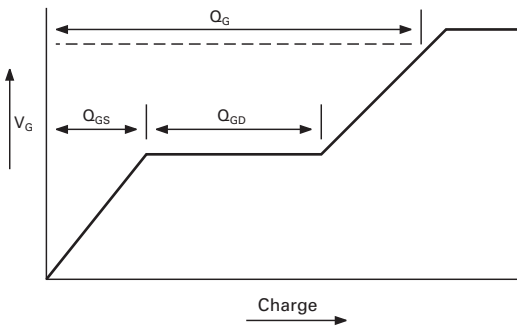


**Capacitance v Drain-Source Voltage**

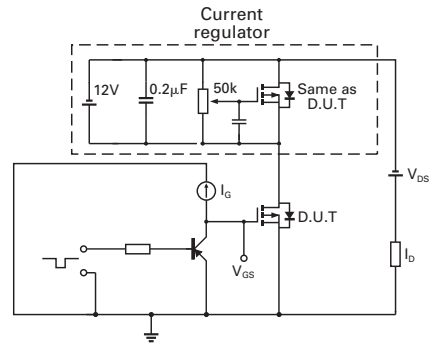


**Gate-Source Voltage v Gate Charge**

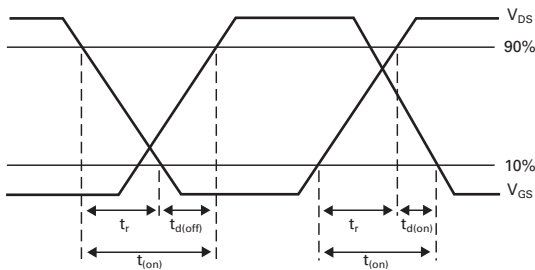
**Test Circuits**



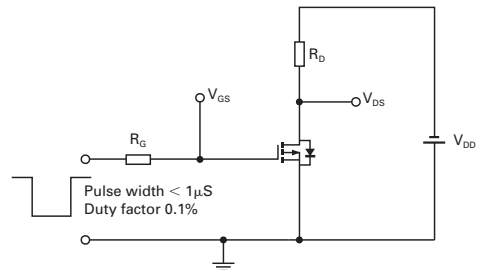
**Basic gate charge waveform**



**Gate charge test circuit**

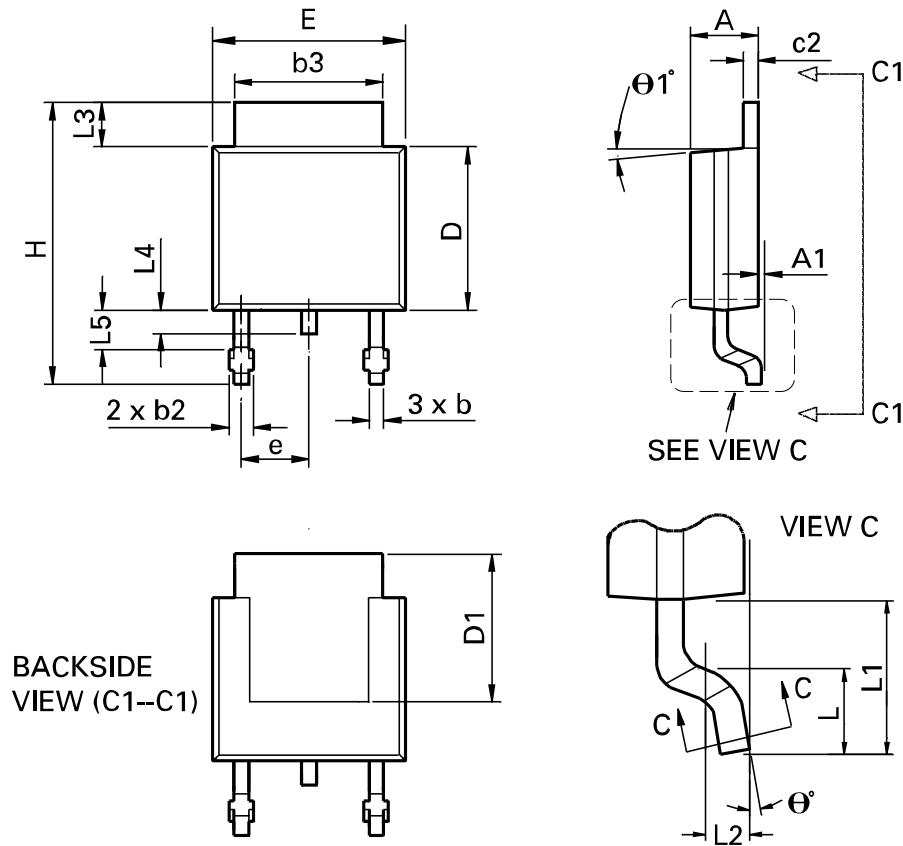


**Switching time waveforms**



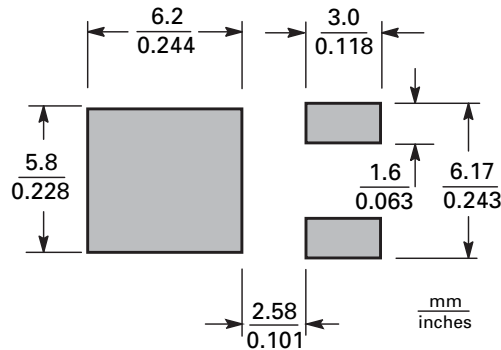
**Switching time test circuit**

**Package Outline Dimensions**



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	e	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	H	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	theta1	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	theta	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

## Suggested Pad Layout



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